This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims

- 1. (original): A selective wetting material comprising a film on a substrate, the film formed from a two-component plasma reaction in a substantially air-evacuated plasma chamber, a first component of the two-component plasma reaction comprising a non-carbon containing and non-oxygenated silicon donor, and a second component of the two-component plasma reaction comprising a non-silicon containing and non-oxygenated organic precursor, the film having a one or more selective wetting regions formed from the exposure of the one or more selective wetting regions to a radiated electromagnetic energy in the presence of oxygen, whereby a liquid brought into contact with the film selectively wets and adheres to the one or more selective wetting regions of the film.
- 2. (original): The selective wetting material of claim 1 wherein the second component of the two-component plasma reaction is selected from the group consisting of alkanes, alkenes, alkynes, phenyls and aromatic hydrocarbons.
- 3. (original): The selective wetting material of claim 1 wherein the second component of the two-component plasma reaction is selected from the group consisting of ethylene, methane, ethane and toluene.
- 4. (original): The selective wetting material of claim 1 wherein the first component of the two-component plasma reaction is selected from the group consisting of monosilane, disilane and dichlorsilane.
- 5. (original): The selective wetting material of claim 4 wherein the second component of the two-component plasma reaction is selected from the group consisting of ethylene, methane, ethane and toluene.

6 - 20. (canceled)

- 21. (new): The selective wetting material of claim 1 wherein the radiated electromagnetic energy is ultraviolet light.
- 22. (new): A selective wetting material comprising a film on a substrate, the film formed from a two-component plasma reaction in a substantially air-evacuated plasma chamber, a first component of the two-component plasma reaction selected from the group consisting of monosilane and disilane, and a second component of the two-component





plasma reaction comprising a non-silicon containing and non-oxygenated organic precursor, the film having a one or more selective wetting regions formed from the exposure of the one or more selective wetting regions to a radiated electromagnetic energy in the presence of oxygen, whereby a liquid brought into contact with the film selectively wets and adheres to the one or more selective wetting regions of the film.

- 23. (new): The selective wetting material of claim 22 wherein the organic precursor is ethylene or toluene.
- 24. (new): The selective wetting material of claim 23 wherein the ratio of silicon atoms to carbon atoms in the film is approximately 1:7.
- 25. (new): The selective wetting material of claim 22 wherein the organic precursor is ethylene or toluene and the silicon donor is monosilane with a weight ratio of the organic precursor to the silicon donor of approximately between 1:2 and 1:1.
- 26. (new): The selective wetting material of claim 22 wherein the organic precursor is selected from the group consisting of alkanes, alkenes, alkynes, phenyls and aromatic hydrocarbons.
- 27. (new): The selective wetting material of claim 22 wherein the radiated electromagnetic energy is ultraviolet light.
- 28. (new): A selective wetting material comprising a film on a substrate, the film formed from a two-component plasma reaction in a substantially air-evacuated plasma chamber, wherein the two components comprise monosilane and an organic precursor selected from the group consisting of ethylene and toluene, the film having a one or more selective wetting regions formed from the exposure of the one or more selective wetting regions to a radiated electromagnetic energy in the presence of oxygen, whereby a liquid brought into contact with the film selectively wets and adheres to the one or more selective wetting regions of the film.
- 29. (new): The selective wetting material of claim 28 wherein the weight ratio of the organic precursor to the monosilane is approximately between 1:2 and 1:1 and the ratio of silicon atoms to carbon atoms in the layer of the film is approximately 1:7.
- 30. (new): The selective wetting material of claim 28 wherein the radiated electromagnetic energy is ultraviolet light.

